

RL78/I1A

RENESAS MCU

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True Low Power Platform, High Resolution PWM and Rich Analog, 2.7 V to 5.5 V operation, 32 to 64 Kbyte Flash, for Inverter Control, Digital Power Control and Lighting Control Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.7 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μ A, (LVD enabled): 0.31 μ A
- Halt (RTC + LVD): 0.60 μA
- Operating: 156.25 μA/MHz

16-bit RL78 CPU Core

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- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC architecture (Harvard) with 3-stage pipeline
- Multiply signed & unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- Density: 32 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data flash with background operation
- Data flash size: 4 KB
- Erase cycles: 1 million (typ.)
- Erase/programming voltage: 2.7 V to 5.5 V

RAM

- 2 KB to 4 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 32 MHz with +/- 1% accuracy over voltage (2.7 V to 5.5 V) and temperature (-20°C to 85°C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 6 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

16-bit timers KB0 to KB2, and KC0 for PWM output

16-bit timers KB0 to KB2: maximum 6 outputs (3 channels × 2)

- Smooth start function, dithering function, forced output stop function (unsynchronized with comparator or external interrupt) enables over-voltage protection, over-current protection and peak current control, and single/interleave PFC function
- Average resolution < 0.98 nsec output, 64 MHz (when using PLL) + dithering option

16-bit timer KC0 (1 channel × 6 (output))

 PWM output gating function by interlocking with 16-bit timers KB0, KB1, and KB2

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Multiple Communication Interfaces

- Up to 1 channel x I²C multi-master (SMBus/PMBus support)
- Up to 1 channel x CSI/SPI (7-, 8-bit)
- Up to 3 channels x UART (7-, 8-, 9-bit),
 DALI support 1 channel (8-, 16-, 17-, 24-bit, master and slave)
- Up to 1 channel x LIN

Rich Analog

- ADC: Up to 11 channels, 8/10-bit resolution, 2.125 μ s conversion time
- Supports 2.7 V
- Internal voltage reference (1.45 V)
- Comparator: High response time 70 ns (typ.), up to 6 channels, internal DAC 3 channels 8-bit resolution, window comparator mode
- PGA (x4 to x32): 6 input channels
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM/SFR write protection
- Illegal memory access detection
- Clock stop/frequency detection
- ADC self-test

General Purpose I/O

- 5-V tolerant, high-current (up to 8.5 mA per pin)
- Open-drain, internal pull-up support

Operating Ambient Temperature

- Standard: -40°C to +105°C
- Extend: -40°C to +125°C

Package Type and Pin Count

SSOP: 20, 30, 38



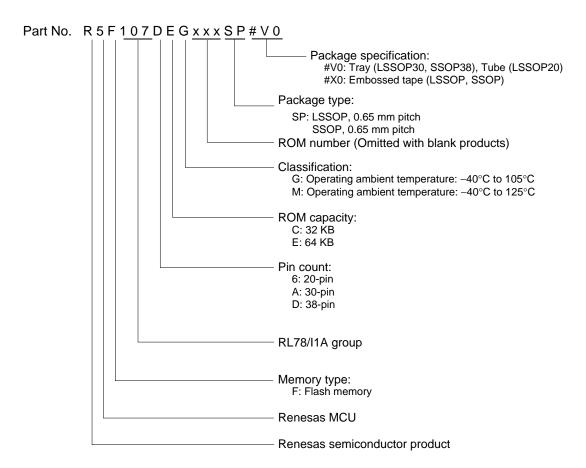
o ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/I1A				
			20 pins	30 pins	38 pins		
64 KB	4 KB	4 KB Note	-	R5F107AE	R5F107DE		
32 KB	4 KB	2 KB	R5F1076C	R5F107AC	-		

Note This is about 3 KB when the self-programming function and data flash function are used.

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/I1A



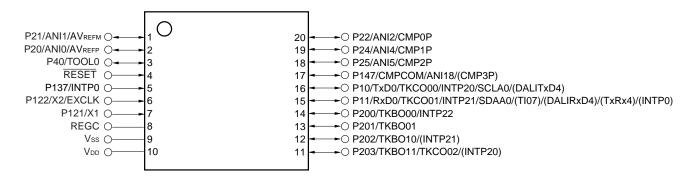
Pin count	Package	Operating Ambient Temperature	Part Number
20 pins	20-pin plastic LSSOP	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F1076CGSP#V0, R5F1076CGSP#X0
	(4.4 × 6.5)	T _A = -40 to +125°C	R5F1076CMSP#V0, R5F1076CMSP#X0
30 pins	30-pin plastic LSSOP (7.62 mm (300))	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0
		T _A = -40 to +125°C	R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0
38 pins	38-pin plastic SSOP	Ta = -40 to +105°C	R5F107DEGSP#V0, R5F107DEGSP#X0
	(7.62 mm (300))	T _A = -40 to +125°C	R5F107DEMSP#V0, R5F107DEMSP#X0

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (4.4 x 6.5)

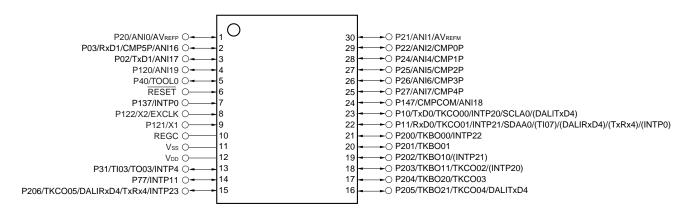


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
 - **3.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.3.2 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300))

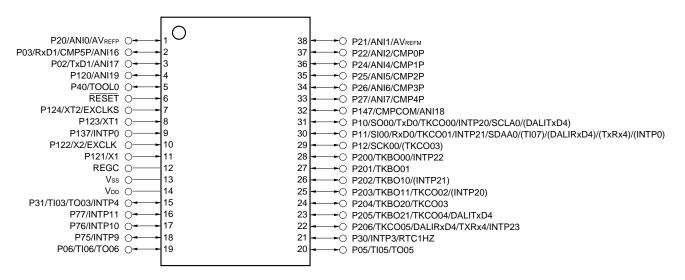


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.3.3 38-pin products

• 38-pin plastic SSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.4 Pin Identification

ANI0 to ANI2, REGC: Regulator Capacitance ANI4 to ANI7, RESET: Reset ANI16 to ANI19: RTC1HZ: Real-time Clock Correction Clock Analog Input Analog Reference Voltage Minus (1 Hz) Output AVREFM: AVREFP: Analog Reference Voltage Plus RxD0, RxD1, CMP0P to CMP5P: Comparator Analog Input DALIRxD4: Receive Data CMPCOM: Comparator External Reference SCK00: Serial Clock Input/Output SCLA0: Serial Clock Input/Output Voltage EXCLK: External Clock Input (Main System SDAA0: Serial Data Input/Output SI00: Serial Data Input **EXCLKS**: SO00: External Clock Input (Subsystem Serial Data Output Clock) TI03, TI05, TI06, INTP0, INTP3, TI07: Timer Input INTP4, INTP9, TO03, TO05, TO06, INTP10, INTP11, TKBO00, TKBO01 to INTP20 to INTP23: Interrupt Request from Peripheral TKBO20, TKBO21, P02, P03, TKCO00 to TKCO05: Timer Output P05, P06: Port 0 TOOL0: Data Input/Output for Tool P10 to P12: Port 1 TxRx4: Serial Data Input/Output for Single P20 to P22, Wired UART P24 to P27: Port 2 TxD0, TxD1 P30, P31: Port 3 DALITxD4: Transmit Data P40: Port 4 V_{DD}: Power Supply

Port 7 Vss: Ground

Port 12 X1, X2: Crystal Oscillator (Main System Clock)

Port 13 XT1, XT2: Crystal Oscillator (Subsystem Clock)

P75 to P77:

P137:

P147:

P120 to P124:

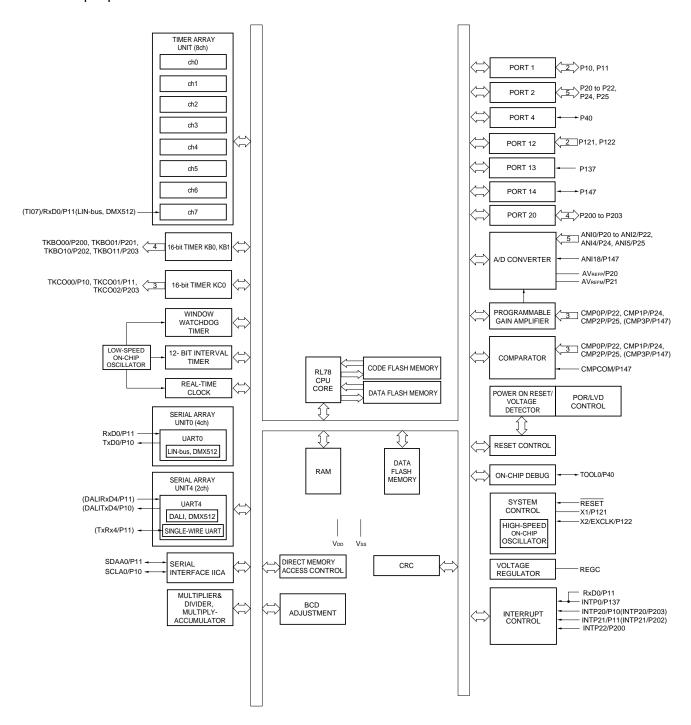
P200 to P206:

Port 14

Port 20

1.5 Block Diagram

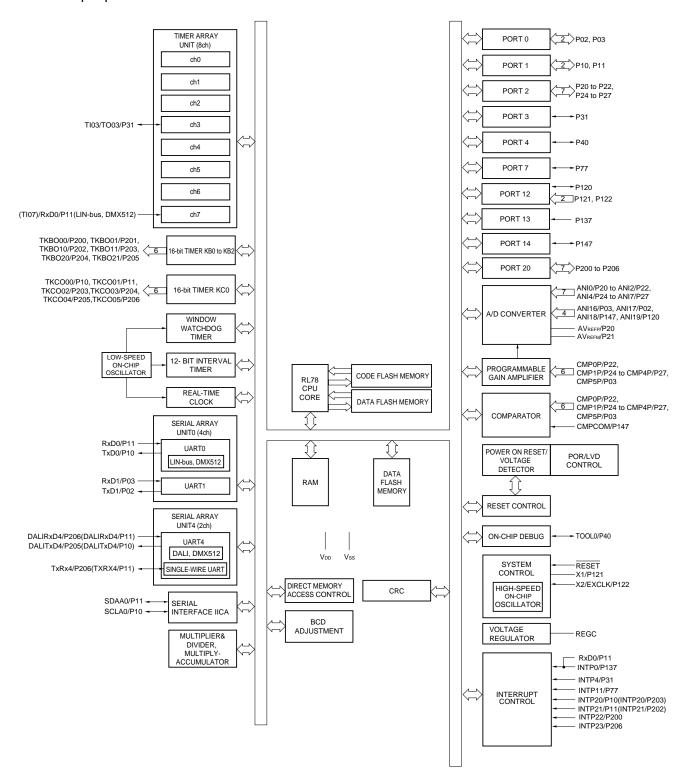
1.5.1 20-pin products



Remarks 1. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

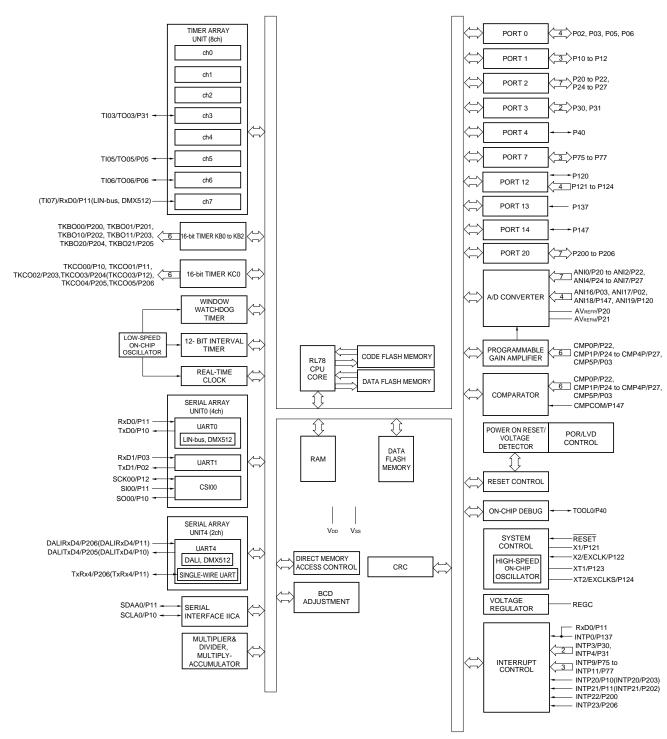
2. The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.5.3 38-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR1) is set to 00H.

(1/3)

	Item	20-pin	3()-pin	38-pin		
	itom	R5F1076C	R5F107AC	R5F107AE	R5F107DE		
0 1 5 1	((5)			+			
Code flash me		32	32	64	64		
Data flash me	emory (KB)	4	4	4	4		
RAM (KB)		2	2	4 ^{Note 1}	4 ^{Note 1}		
Address space	e	1 MB					
Main system clock	High-speed system clock	X1 (crystal/ceramic) osc HS (High-speed main) r LS (Low-speed main) m	mode: 1 to 20 MHz (VDE	-			
	High-speed on-chip oscillator	HS (High-speed main) r	·	-			
Clock for 16-b and KC0	oit timers KB0 to KB2,	64 MHz (TYP.)					
Subsystem cloonly)	ock (38-pin products	XT1 (crystal) oscillation 32.768 kHz	, external subsystem clo	ock input (EXCLKS)			
Low-speed or	n-chip oscillator	15 kHz (TYP.)					
General-purp	ose register	(8-bit register × 8) × 4 banks					
Minimum insti	ruction execution time	$0.03125 \mu s$ (High-speed on-chip oscillator: f_{H} = 32 MHz operation)					
		$0.05 \mu s$ (High-speed system clock: f _{MX} = 20 MHz operation)					
		30.5 μs (Subsystem clock: fsub = 32.768 kHz operation) (38-pin products only)					
Instruction se	t	 8-bit operation, 16-bit operation Multiplication (8 bits × 8 bits) Bit manipulation (Set, reset, test, and Boolean operation), etc. 					
I/O port	Total	16		26	34		
	CMOS I/O	13		23	29		
	CMOS input	3		3	5		
	CMOS output	-		-	-		
Timer	16-bit timer TAU	8 channels (no timer output)	8 channels (timer outpu	ut: 1, PWM output: 1 ^{Note 2})	8 channels (timer outputs: 3, PWM outputs: 3 ^{Note 2})		
	16-bit timer KB	2 channels (PWM outputs: 6) outputs: 4)					
	16-bit timer KC	1 channel (PWM outputs: 3)	1 channel (PWM outputs: 6)				

- **Notes 1.** This is about 3 KB when the self-programming function and data flash function are used. (For details, see **CHAPTER 3 in the RL78/I1A User's Manual**.)
 - The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/I1A User's Manual).

(2/3)

				,	(2/3)			
	Item		20-pin	30-pin	38-pin			
			R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Timer	Watchdo	g timer	1 channel					
	Real-time (RTC)	clock		1 channel ^{Notes 1, 2}				
	12-bit inte	erval timer		1 channel				
	RTC outp	ut		-	1 1 Hz (subsystem clock: fsub = 32.768 kHz)			
8/10-bit resoluti	on A/D co	onverter	6 channels	11 channels	11 channels			
Comparator			4 channels	6 channels	6 channels			
Programmable	gain amp	lifier		1 channel				
		Input ^{Note 3}	4 channels	6 channels	6 channels			
Serial interface		<u> </u>	[20-pin] Note 5					
			UART (Supporting LII)	N-bus and DMX512): 1 channel				
				UART (Supporting DALI communication): 1 channel				
			[30-pin products]					
			UART (Supporting LIN-bus and DMX512): 1 channel					
			• UART: 1 channel					
			UART (Supporting DA)	ALI communication): 1 channel				
			[38-pin products]	•				
				(Supporting LIN-bus and DMX512): 1 channel				
			UART: 1 channel					
	1		UART (Supporting D/	ALI communication): 1 channel	1			
	I ² C b	us	1 channel	1 channel	1 channel			
Multiplier and d accumulator	vider/mul	Itiply-	• 32 bits ÷ 32 bits = 32 l	bits (Unsigned or signed) bits (Unsigned) bits = 32 bits (Unsigned or signed)				
DMA controller				2 channels				
Vectored interru	ıpt Interr	nal	27	30	30			
sources	Exter		7	10	11			
Reset	1		Reset by RESET pin		•			
			Internal reset by watch	=				
			Internal reset by power					
			Internal reset by volta	<u> </u>				
1				al instruction execution ^{Note 4} Il parity error				
İ			Internal reset by RAM parity error Internal reset by illegal-memory access					
			Internal reset by illegal-memory access					

Notes 1. The subsystem clock (fsub) can be selected as the operating clock only for 38-pin products.

- 2. The 20- and 30-pin products can only be used as the constant-period interrupt function.
- 3. The comparator input is alternatively used with analog input pin (ANI pin).
- 4. The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.
- 5. The 20 pin products can only be used 1 UART simultaneously due to sharing of the same I/O pins.

(3/3)

			(0/0)			
Item	20-pin	30-pin	38-pin			
	R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)				
Voltage detector	= =	, , ,				
On-chip debug function	Provided					
Power supply voltage	V _{DD} = 2.7 to 5.5 V					
Operating ambient temperature	$T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications), $T_A = -40 \text{ to } +125^{\circ}\text{C}$ (M: Industrial applications)					

2. ELECTRICAL SPECIFICATIONS

(G: Industrial applications, $T_A = -40$ to +105°C)

In this chapter, shows the electrical specifications of the target products.

Target products (G: Industrial applications): $T_A = -40 \text{ to } + 105^{\circ}\text{C}$ R5F107xxGxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation.

 Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	٧
REGC pin input voltage	Virego	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	>
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	٧
Analog input voltage	Val1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(*)} +0.3 ^{Notes 2, 3}	٧

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **2.** $AV_{REF(+)}$: + side reference voltage of the A/D converter.
- 3. Vss: Reference voltage

Absolute Maximum Ratings ($T_A = 25$ °C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		–170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins	P02, P03, P40, P120	70	mA
		170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lo _{L2}	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory p	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/crystal resonator		1.0		20.0	MHz
XT1 clock oscillation frequency (fxt)Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see **5.4 System Clock Oscillator in the RL78/I1A**User's Manual.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator		T _A = -20 to 85°C	-1		+1	%
clock frequency accuracyNote 2		T _A = -40 to 105°C	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fiL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

2.2.3 PLL characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	f _{PLLIN}	High-speed system clock is selected (f _{MX} = 4 MHz)	3.94	4.00	4.06	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f _{IH} = 4 MHz)	3.94	4.00	4.06	MHz
PLL output clock frequency ^{Note}	fpll			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{DD} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	2.7 V ≤ V _{DD} < 4.0 V			-1.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$) Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$4.0~V \leq V_{DD} \leq 5.5~V$			-12.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-4.0	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-10.0	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			-14.0	mA
	Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			-0.7	mA

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and $I_{OH} = -10.0$ mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	l _{OL1}	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{DD} \leq 5.5~V$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			7.5	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty ≤ 70% ^{Note 3}) Total of all pins	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			17.5	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			80.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			25.0	mA
lo _{L2}	lo _{L2}	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			2.8	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	Voltage, V _{IH1} P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET		Normal input buffer	0.8V _{DD}		V _{DD}	V
V _{IH2}		P03, P10, P11	TTL input buffer $4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	V _{IL2}	P03, P10, P11	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer $3.3 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -3.0 \text{ mA}$	V _{DD} - 0.7			V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low	Vol1	P31, P40, P75 to P77, P120, P147, P200 to P206	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 8.5 \text{ mA}$			0.7	V
			$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 4.0 \text{ mA}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 1.5 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{DD}				1	μA
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μΑ
Input leakage current, low	Iuli	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{SS}				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pull-up resistance	R∪	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	V _I = V _{SS} , In input port		10	20	100	kΩ

2.3.2 Supply current characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 32 MHz ^{Note 3}	V _{DD} = 5.0 V		5.0	7.5	mA
current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		5.0	7.5	mA
			mode ***	f _{IH} = 24 MHz ^{Note 3}	V _{DD} = 5.0 V		3.9	5.8	mA
					V _{DD} = 3.0 V		3.9	5.8	mA
				f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.2	mA
					V _{DD} = 3.0 V		2.9	4.2	mA
			LS (low-	f _{IH} = 8 MHz ^{Note 3} ,	V _{DD} = 3.0 V		1.3	2.0	mA
			speed main) mode ^{Note 5}	TA = -40 to + 85°C					
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	4.9	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.0	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Square wave input		3.2	4.9	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.0	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Square wave input		2.0	2.9	mA	
				V _{DD} = 5.0 V	Resonator connection		2.0	2.9	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Square wave input		2.0	2.9	mA	
			V _{DD} = 3.0 V	Resonator connection		2.0	2.9	mA	
			LS (low-	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$	Square wave input		1.2	1.8	mA
			speed main) mode ^{Note 5}	$V_{DD} = 3.0 \text{ V},$ $T_A = -40 \text{ to } + 85^{\circ}\text{C}$	Resonator connection		1.2	1.8	mA
			HS (high- speed main) mode ^{Note 5}	f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		5.4	8.5	mA
				fpll = 64 MHz, fclk = 32 MHz	V _{DD} = 3.0 V		5.4	8.5	mA
				f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	5.7	mA
				fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		3.3	5.7	mA
			Subsystem	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA
			clock operation	T _A = -40°C	Resonator connection		4.4	6.2	μА
			Орегацоп	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μА
				T _A = +25°C	Resonator connection		4.4	6.2	μА
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μΑ
				T _A = +50°C	Resonator connection		4.5	7.4	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA
			T _A = +70°C	Resonator connection		4.6	8.3	μА	
			fsuB = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA	
			T _A = +85°C	Resonator connection		5.4	11.6	μА	
			fsub = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μА	
				T _A = +105°C	Resonator connection		7.1	21.0	μА

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$ to 32 MHz LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$ to 8 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2} Note 2	HALT	HS (high-	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA
current		mode	speed main)		V _{DD} = 3.0 V		0.72	2.9	mA
Note 1			mode ^{Note 7}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA
					V _{DD} = 3.0 V		0.57	2.3	mA
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA
					V _{DD} = 3.0 V		0.50	1.7	mA
			LS (low- speed main) mode ^{Note 7}	f _{IH} = 8 MHz ^{Note 4} , T _A = -40 to +85°C	V _{DD} = 3.0 V		320	910	μΑ
			HS (high-	f _{MX} = 20 MHz ^{Note 3} , Square wave inp			0.40	1.9	mA
			speed main)	V _{DD} = 5.0 V	Resonator connection		0.50	2.0	mA
			mode ^{Note 7}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.0	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	mA
				V _{DD} = 5.0 V	Resonator connection		0.30	1.08	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	mA
			LS (low- speed main) mode ^{Note 7}	V _{DD} = 3.0 V	Resonator connection		0.30	1.08	mA
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		130	720	μА
				$V_{DD} = 3.0 \text{ V},$ $T_A = -40 \text{ to } +85^{\circ}\text{C}$	Resonator connection		170	760	μΑ
			HS (high-	f _H = 4 MHz ^{Note 4}	V _{DD} = 5.0 V		1.15	4.0	mA
			speed main)	fPLL = 64 MHz, fcLK = 32 MHz	V _{DD} = 3.0 V		1.15	4.0	mA
			mode ^{Note 7}	f _H = 4 MHz ^{Note 4}	V _{DD} = 5.0 V		0.95	3.2	mA
				fPLL = 64 MHz, fCLK = 16 MHz	V _{DD} = 3.0 V		0.95	3.2	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μА
				T _A = -40°C	Resonator connection		0.47	0.89	μА
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μА
				T _A = +25°C	Resonator connection		0.52	0.89	μА
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.41	1.90	μА
				T _A = +50°C	Resonator connection		0.60	2.09	μА
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.54	2.80	μА
				T _A = +70°C	Resonator connection		0.73	2.99	μА
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μΑ
				T _A = +85°C	Resonator connection		1.46	6.29	μА
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μА
				T _A = +105°C	Resonator connection		3.23	15.7	μΑ
	I _{DD3} Note 6	STOP	T _A = -40°C				0.18	0.50	μΑ
		mode	T _A = +25°C				0.23	0.50	μΑ
		Note 8	T _A = +50°C				0.27	1.70	μΑ
			T _A = +70°C T _A = +85°C				0.44	2.60	μΑ
							1.17	5.90	μΑ
	<u></u>		T _A = +105°C				2.94	15.3	μА

(Notes and Remarks are listed on the next page.)



- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 32 MHz LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 8 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fih: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FILNote 1						0.20		μА
RTC operating current	RTC Notes 1, 2, 3						0.02		μА
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	Notes 1, 2, 5	fı∟ = 15 kHz					0.22		μА
A/D converter operating current	ADC Notes 1, 6	When conversion maximum speed			$AV_{REFP} = V_{DD} = 5.0 \text{ V}$ node, $AV_{REFP} = V_{DD} = 3.0 \text{ V}$		1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	I _{ADREF} Note 1						75.0		μΑ
Temperature sensor operating current	I _{TMPS} Note 1						75.0		μА
LVD operating current	LVDNotes 1, 7								μА
Self- programming operating current	FSPNotes 1, 8						2.50	12.2	mA
Programmable gain amplifier operating current	I _{PGA} Note 9				$AV_{REFP} = V_{DD} = 5.0 \text{ V}$ $AV_{REFP} = V_{DD} = 3.0 \text{ V}$		0.21	0.31	mA mA
Comparator	ICMPNote 10	When one comp	parator	channel is	AV _{REFP} = V _{DD} = 5.0 V		41.4	62	μА
operating current		operating			AV _{REFP} = V _{DD} = 3.0 V		37.2	59	μА
	IVREF	When one interr		erence voltage	AV _{REFP} = V _{DD} = 5.0 V		14.8	26	μA
		circuit is operation	ng		AV _{REFP} = V _{DD} = 3.0 V		8.9	20	μA
Programmable	IREF Note 11				AV _{REFP} = V _{DD} = 5.0 V		3.2	5.1	μA
gain amplifier/ comparator reference current source					AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μA
BGO operating current	I _{BGO} Note 12						2.50	12.2	mA
SNOOZE I _{SNOZ} Note 1 ADC operation The mode is perform			ed ^{Note 13}		0.50	1.1	mA		
operating current			The A/D conversion operations are performed, Standard mode, AV _{REFP} = V _{DD} = 5.0 V				2.0	3.04	mA
		CSI/UART opera	ation				0.70	1.54	mA

(Notes and Remarks are listed on the next page.)

- Notes 1. Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - **4.** Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and f_{IL} operating current). The current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode.
 - **5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
 - **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - **8.** Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - **12.** Current flowing only during data flash rewrite.
 - 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode .
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$
 - **5.** Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

```
ICMP × 3 + IVREF + IPGA + IREF
= 41.4 [\mu A] × 3 + 14.8 [\mu A] × 1 + 210 [\mu A] + 3.2 [\mu A]
= 352.2 [\mu A]
```

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

```
ICMP × 2 + IIREF
= 41.4 [\mu A] × 2 + 3.2 [\mu A]
= 86.0 [\mu A]
```

2.4 AC Characteristics

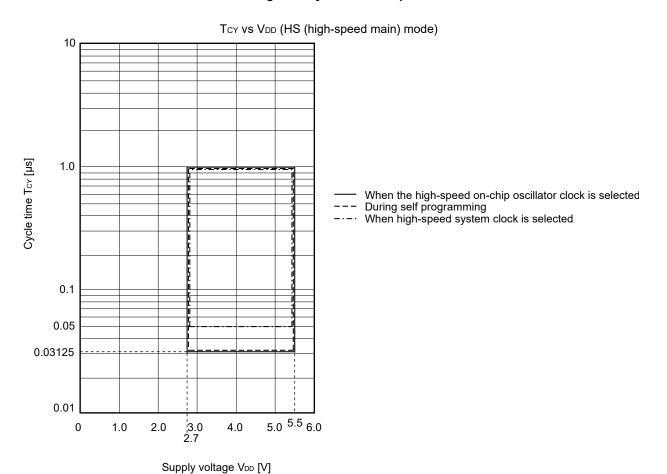
(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

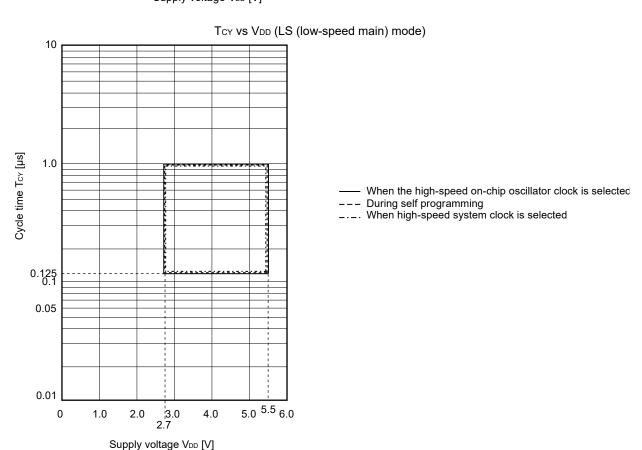
Items	Symbol		Conditio	ns		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main system	HS (high-spe	HS (high-speed main) mode		0.03125		1	μS
instruction execution time)		clock (fmain) operation	LS (low-spee		$T_A = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
		Subsystem clo	ck (fsuв) ор	erati	on	28.5	30.5	31.3	μS
		In the self	HS (high-spe	eed n	nain) mode	0.03125		1	μS
		programming mode	LS (low-spee		$T_A = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
External system clock frequency	fex					1.0		20.0	MHz
	fexs					32		35	kHz
External system clock input high-	texh, texl					24			ns
level width, low-level width	texhs, texhs					13.7			μS
TI03, TI05, TI06, TI07 input high-level width, low-level width	tтıн, tтı∟					2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	f то	HS (high-speed main)		4.0	$V \leq V_{DD} \leq 5.5~V$			8	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to		mode		2.7	$V \le V_{DD} \le 4.0 V$			4	MHz
TKCO05 output frequency		LS (low-speed		4.0	$V \leq V_{DD} \leq 5.5~V$			4	MHz
(When duty = 50%)		mode, $T_A = -40 \text{ to } +85^{\circ}\text{C}$		2.7	$V \le V_{DD} \le 4.0 V$			2	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23			1			μS	
RESET low-level width	trsl					10			μS

Remark fmck: Timer array unit operation clock frequency

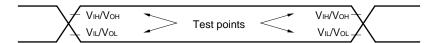
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

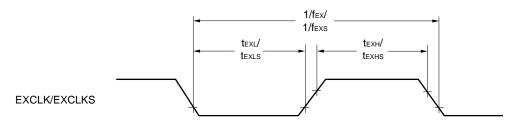




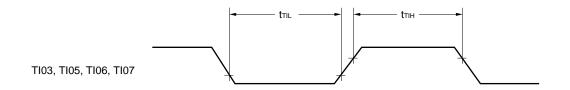
AC Timing Test Points

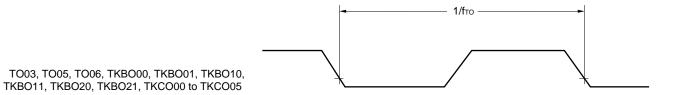


External System Clock Timing

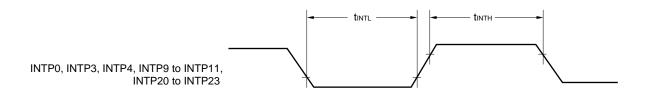


TI/TO Timing

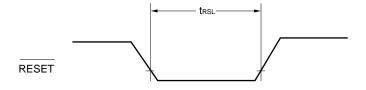




Interrupt Request Input Timing

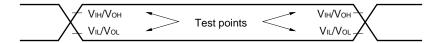


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



- 2.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)
- (1) During communication at same potential (UART mode) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		2.7 V≤ V _{DD}	2.7 V≤ V _{DD} ≤ 5.5 V		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

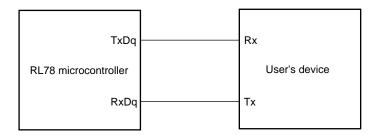
2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

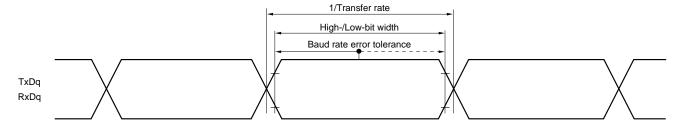
LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}), \text{ T}_{A} = -40 \text{ to } +85^{\circ}\text{C}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 5}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions HS (high-speed main) Mode		` '	LS (low-speed main) Mode			
			MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t KCY1	tkcy1 ≥ 4/fclk	125		500		ns	
SCKp high-/low-level	t кн1,	$4.0~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 12		tkcy1/2 - 50		ns	
width	t KL1	$2.7~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 18		tkcy1/2 - 50		ns	
SIp setup time (to SCKp [↑])	tsıĸ1	$4.0~V \leq V_{DD} \leq 5.5~V$	44		110		ns	
Note 1		$2.7~V \leq V_{DD} \leq 5.5~V$	44		110		ns	
SIp hold time (from SCKp [↑]) Note 2	tksi1		19		19		ns	
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}		25		25	ns	

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
 - **5.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

fMCK: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 6}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-spee	Unit	
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \le V_{DD} \le 5.5~V$	20 MHz < f _{MCK}	8/fмск		_		ns
Note 5			fмcк ≤ 20 MHz	6/fмск		6/fмск		ns
		$2.7~V \le V_{DD} \le 5.5~V$	16 MHz < fмск	8/fмск		-		ns
			fмcк ≤ 16 MHz	6/fмск		6/fмск		ns
SCKp high-/low-level width	t _{KH2} ,			tkcy2/2		tkcy2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık2			1/fмск+20		1/fмск+30		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksı2			1/fмск+31		1/fмск+31		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso2	C = 30 pF ^{Note 4}			2/fмск+ 44		2/fмск+ 110	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - **6.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to $+85^{\circ}$ C.

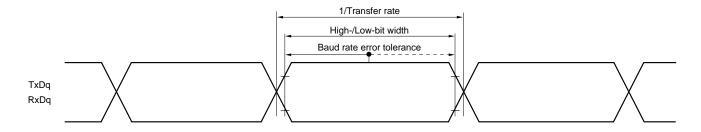
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

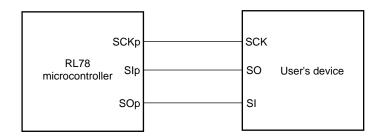
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

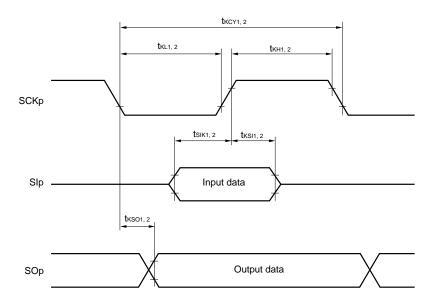
n: Channel number (mn = 00))



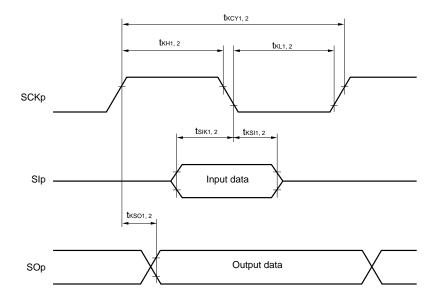
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			peed main) ode		peed main) ode	Unit
						MAX.	MIN.	MAX.	
Transfer		Reception	4.0 V	$V \le V_{DD} \le 5.5 \text{ V}, \ 2.7 \text{ V} \le V_{b} \le 4.0 \text{ V}$		fmck/6 ^{Note 1}		fmck/6 ^{Note 1}	bps
rate				Theoretical value of the maximum transfer rate fmck = fclk Note 2		5.3		1.3	Mbps
			2.7 V	$1 \le V_{DD} \le 4.0 \text{ V}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$		fmck/6 ^{Note 1}		fmck/6 ^{Note 1}	bps
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 2}		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}), \text{ T}_{A} = -40 \text{ to } +85^{\circ}\text{C}.$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). $\,$ m: Unit number,

n: Channel number (mn = 00 to 03)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 5}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode	
					MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V	$V \le V_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le V_{b} \le 4.0 \text{ V}$		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
			2.7 V	$V \leq V_{DD} \leq 4.0 \text{ V}, 2.3 \text{ V} \leq V_{b} \leq 2.7 \text{ V}$		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0~V \le V_{DD} \le 5.5~V$ and $2.7~V \le V_{b} \le 4.0~V$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b})\} \times 3} [bps]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{|\text{Transfer rate} \times 2|} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{|V_b|})\}}{(\frac{1}{|\text{Transfer rate}|}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to $+85^{\circ}$ C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

 $\textbf{Remarks 1.} \quad \mathsf{Rb}[\Omega] \text{: } \mathsf{Communication line (TxDq) pull-up resistance,}$

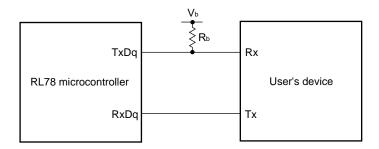
C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

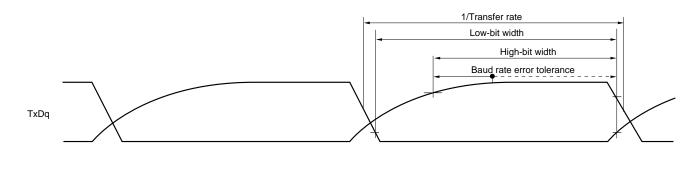
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

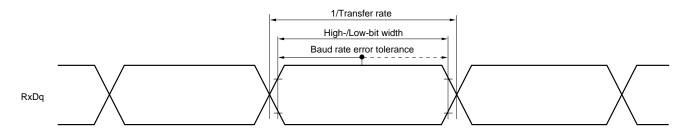
m: Unit number, n: Channel number (mn = 00 to 03))

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 3}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high main) N	•	LS (low-s	•	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 2/f cLK	$\begin{aligned} 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	200		1150		ns
			$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	300		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{V}_{DD} \leq$ $C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tkcy1/2 - 50		tkcy1/2 - 75		ns
		$2.7~V \leq V_{DD} \leq$ $C_b = 30~pF,~F$	$4.0~V,~2.3~V \leq V_b \leq 2.7~V,$ $R_b = 2.7~k\Omega$	tксу1/2 — 120		tkcy1/2 – 170		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tkcy1/2 - 7		tkcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tkcy1/2 - 10		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$4.0 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	81		479		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$	177		479		ns
SIp hold time (from SCKp↑)	t _{KSI1}	•	$5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	10		19		ns
Note 1		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	10		19		ns
Delay time from SCKp↓ to SOp	tkso1		$5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		60		100	ns
output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		130		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	44		110		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	44		110		ns
Slp hold time (from SCKp↓)	tksi1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $R_{\text{b}} = 1.4 \text{ k}\Omega$	10		19		ns
Note 2		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_b = 30 \text{ pF, F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	10		19		ns
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$		10		25	ns
SOp outputNote 2			$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		10		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM number (g = 1)

(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 3}, 2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	d main) Mode	LS (low-speed	l main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	t _{KCY1} ≥ 4/f _{CLK}	$\begin{split} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	300		1150		ns
			$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ R_{b} = 1.4 k Ω	tkcy1/2 - 75		tксу1/2 – 75		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tксү1/2 – 170		tkcy1/2 - 170		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, I$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	tксү1/2 – 12		tксү1/2 — 50		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $\text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	tkcy1/2 - 18		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑)	tsıĸ1	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, I	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	81		479		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $R_{\text{b}} = 2.7 \text{ k}\Omega$	177		479		ns
SIp hold time (from SCKp [↑])	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	19		19		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq C_b = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ R_{b} = 1.4 k Ω		100		100	ns
oop output		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		195		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, I$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	44		110		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $\text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	44		110		ns
SIp hold time (from SCKp↓)	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le \text{Cb} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ Rb = 1.4 k Ω	19		19		ns
		$2.7 \text{ V} \le \text{V}_{DD} \cdot \text{Cb} = 30 \text{ pF},$	$<$ 4.0 V, 2.3 V \le V _b \le 2.7 V, Rb = 2.7 kΩ	19		19		ns
Delay time from SCKp↑ to SOp outputNote 2	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le \text{Cb} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ Rb = 1.4 k Ω		25		25	ns
SOp output		2.7 V ≤ V _{DD} · Cb = 30 pF,	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ Rb = 2.7 k Ω		25		25	ns

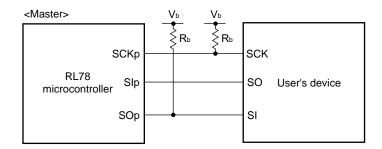
Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

(Caution and Remarks are listed on the next page.)

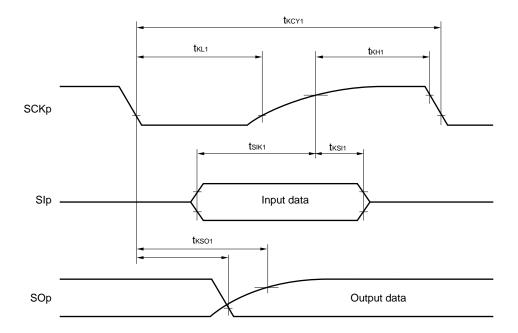
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

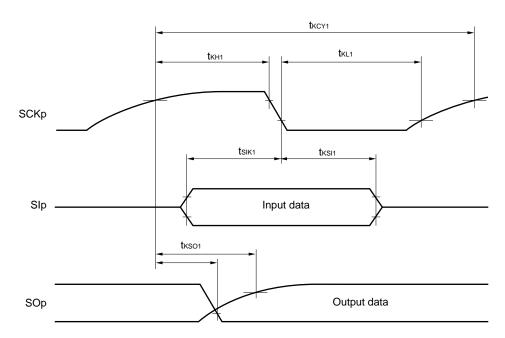


- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(7) DALI/UART4 mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode	
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/12		fмск/12	bps
		Maximum transfer rate theoretical value HS: fclk = 32 MHz, fmck = fclk LS: fclk = 8 MHz, fmck = fclk		2.6		0.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

2.5.2 Serial interface IICA

(1) I²C standard mode

(Ta = -40 to $+105^{\circ}$ C $^{\text{Note 3}}$, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (hig main)		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fclk≥ 1 MHz	0	100	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		4.7		μS
Hold time ^{Note 1}	thd:sta		4.0		4.0		μS
Hold time when SCLA0 = "L"	tLOW		4.7		4.7		μs
Hold time when SCLA0 = "H"	tніgн		4.0		4.0		μS
Data setup time (reception)	tsu:dat		250		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	3.45	μs
Setup time of stop condition	tsu:sto		4.0		4.0		μS
Bus-free time	t BUF		4.7		4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

(2) I²C fast mode

$(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note 3}}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

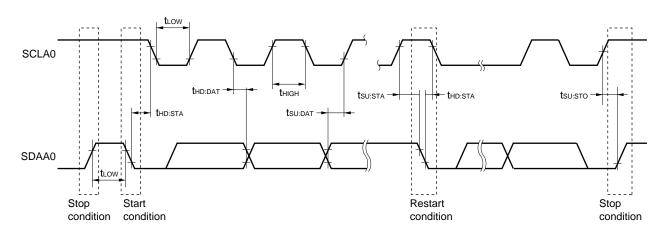
Parameter	Symbol	Conditions	HS (hig main)	•	LS (low main)	•	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fcLκ ≥ 3.5 MHz	0	400	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		0.6		μS
Hold time ^{Note 1}	thd:STA		0.6		0.6		μS
Hold time when SCLA0 = "L"	tLOW		1.3		1.3		μS
Hold time when SCLA0 = "H"	tніgн		0.6		0.6		μS
Data setup time (reception)	tsu:dat		100		100		ns
Data hold time (transmission)Note 2	thd:dat		0	0.9	0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		0.6		μS
Bus-free time	t BUF		1.3		1.3		μS

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
 - 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

	Reference Voltage							
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}					
ANI0 to ANI2, ANI4 to ANI7	See 2.6.1 (1).	See 2.6.1 (3).	See 2.6.1 (4).					
ANI16 to ANI19	See 2.6.1 (2).							
Internal reference voltage Temperature sensor output voltage	See 2.6.1 (1).		-					

(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Parameter	Symbol	Condition	ıs	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} Note 4		V
		Temperature sensor output v (HS (high-speed main) mode	•	\	/TMPS25 ^{Note}	4	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +105°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}			1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +105°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.1875		39	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.5625		39	μs
		main) mode)					
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _F s	10-bit resolution				±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution				±4.0	LSB
Differential linearity errorNote 1	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI2, ANI4 to ANI7	7	0		V_{DD}	V
		ANI16 to ANI19		0		V_{DD}	V
		Internal reference voltage (HS (high-speed main) mod	e)		V _{BGR} Note 3		V
		Temperature sensor output (HS (high-speed main) mod	· ·	\	/ _{TMPS25} Note	3	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(T_A = -40 to +105°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}Note 3, Reference voltage (-) = AV_{REFM} = 0 V^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity errorNote 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		V _{BGR} Note 3	٧

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.
 - **4.** When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	V _{BGRT}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

2.6.3 Programmable gain amplifier

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 times					±1.5	%
		32 time	s			±2	%	
Slew rate ^{Note 1}		Rising edge	•	4, 8 times	4			V/μs
				16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SRFPGA	Falling	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 times		5			μs	
		16, 32 t	16, 32 times					μS

Notes 1. When V_{IPGA} = 0.1V_{DD}/gain to 0.9V_{DD}/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

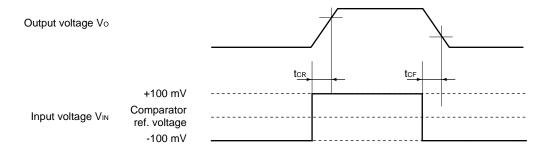
2.6.4 Comparator

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	٧
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcf	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait timeNote 1	tcmp	$3.3~V \leq V_{DD} \leq 5.5~V$	1			μs
		2.7 V ≤ V _{DD} < 3.3 V	3			μs
Reference voltage stabilization wait time	tvR	CVRE: 0 to 1 ^{Note 2}	10			μS

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.

Remark These characteristics apply when AVREFP is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AVREFM is selected as GND of the internal reference voltage by using the CVRVS1 bit.

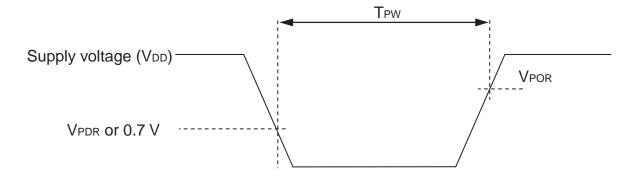


2.6.5 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.97	4.06	4.14	V
voltage			Power supply fall time	3.89	3.98	4.06	V
		V _{LVD1}	Power supply rise time	3.67	3.75	3.82	V
		Power supply fall time	3.59	3.67	3.74	V	
	V _{LVD2}	Power supply rise time	3.06	3.13	3.19	V	
			Power supply fall time	2.99	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.95	3.02	3.08	V
			Power supply fall time	2.89	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.85	2.92	2.97	V
			Power supply fall time	2.79	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pul	se width	tuw		300			μS
Detection de	lay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVD0}	V _{POC2} ,	V _{POC1} , V _{POC0} = 0, 1, 1,	falling reset voltage: 2.7 V	2.70	2.75	2.81	V
mode VLVD1 VLVD2 VLVD3	V _{LVD1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	2.97	V
				Falling interrupt voltage	2.79	2.86	2.91	V
	V _{LVD2}	/LVD2		Rising release reset voltage	2.95	3.02	3.08	V
				Falling interrupt voltage	2.89	2.96	3.02	V
	V _{LVD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.14	V
				Falling interrupt voltage	3.89	3.98	4.06	V

2.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SV _{DD}				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 32.4 AC Characteristics.

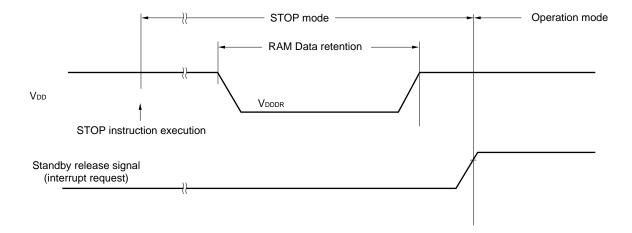
2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltageNote 2	VDDDR		1.44 ^{Note 1}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.



2.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3}	1,000			Times
Number of data flash		Retained for 1 year, T _A = 25°C ^{Note 3}		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, T _A = 85°C ^{Note 3}	100,000			
		Retained for 20 years, T _A = 85°C ^{Note 3}	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

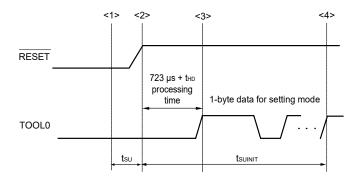
(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

2.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



<R>

- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

3. ELECTRICAL SPECIFICATIONS

(M: Industrial applications, $T_A = -40$ to +125°C)

In this chapter, shows the electrical specifications of the target products.

Target products (M: Industrial applications): $T_A = -40$ to +125°C R5F107xxMxx

NOF IU/XXIVIXX

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.
 - 3. When any of these products are used at 105° C or lower, see 2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +105°C).



3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	>
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	٧
Analog input voltage	Val1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	٧

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF (+)}: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins –170 mA	P02, P03, P40, P120	-70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	І он2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lol1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lol2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal operation	on mode	-40 to +125	°C
temperature		In flash memory p	programming mode	-40 to +105	
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator		1.0		20.0	MHz
XT1 clock frequency (f _{XT}) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracy ^{Note 2}		T _A = -20 to 85°C	-1		+1	%
		T _A = -40 to 105°C	-1.5		+1.5	%
		T _A = -40 to 125°C When 16 MHz selected	-2		+2	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds T_A = 105°C, the selectable oscillation frequency is 16 MHz max.

3.2.3 PLL characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	f _{PLLIN}	High-speed system clock is selected (f _{MX} = 4 MHz)	3.92	4.00	4.08	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f _{IH} = 4 MHz)	3.92	4.00	4.08	MHz
PLL output clock frequency ^{Note}	f _{PLL}			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105^{\circ}C$, only 16 MHz (f_{PLL} × 1/4) can be selected as the CPU operating frequency.

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	І он1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{DD} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			-9.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-3.0	mA
		P75 to P77 P147 P200 to P206	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-6.0	mA
		Total of all pins	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-9.0	mA
	Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			-0.4	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	I _{OL1}	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{DD} \leq 5.5~V$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			5.0	mA
		D75 to D77 D147 D200 to D206	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
			$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			15.0	mA
	lo _{L2}	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			1.6	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8V _{DD}		V _{DD}	>
	V _{IH2}	<u>.</u>	TTL input buffer $4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	V _{IL1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	>
	V _{IL2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -3.0 \text{ mA}$	V _{DD} - 0.7			V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage,	Vol1	P31, P40, P75 to P77, P120, P147, P200 to P206	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 8.5 \text{ mA}$			0.7	V
			$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 4.0 \text{ mA}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ıs		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ісін1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{DD}				1	μΑ
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μΑ
Input leakage current, low	ILIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{SS}				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	V _I = V _{SS} , In input port		10	20	100	kΩ

3.3.2 Supply current characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.8	mA
Current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		2.9	4.8	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.7	mA
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.7	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA
				V _{DD} = 5.0 V	Resonator connection		2.0	3.3	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA
				V _{DD} = 3.0 V	Resonator connection		2.0	3.3	mA
			HS (high-		V _{DD} = 5.0 V		3.3	6.5	mA
			speed main) mode ^{Note 5}	fPLL = 64 MHz, fcLK = 16 MHz	V _{DD} = 3.0 V		3.3	6.5	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 4} T _A = -40°C	Square wave input		4.2	6.0	μА
					Resonator connection		4.4	6.2	μА
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +25°C	Square wave input		4.2	6.0	μА
					Resonator connection		4.4	6.2	μА
				f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μА
				T _A = +50°C	Resonator connection		4.5	7.4	μА
				f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μА
				T _A = +70°C	Resonator connection		4.6	8.3	μА
				fsub = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA
				T _A = +85°C	Resonator connection		5.4	11.6	μA
				f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA
			fs	T _A = +105°C	Resonator connection		7.1	21.0	μA
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +125°C	Square wave input		11.1	51.2	μА
					Resonator connection	_	11.3	51.4	μА

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 20 MHz

- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2} Note 2	HALT	HS (high-	f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.50	2.0	mA
Current Note 1		mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.50	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	2.2	mA
			speed main) mode ^{Note 7}	V _{DD} = 5.0 V	Resonator connection		0.50	2.3	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.40	2.2	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.3	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.22	mA
				V _{DD} = 5.0 V	Resonator connection		0.30	1.28	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.22	mA
				V _{DD} = 3.0 V	Resonator connection		0.30	1.28	mA
			HS (high- speed main) mode ^{Note 7}	f _{IH} = 4 MHz ^{Note 4} f _{PLL} = 64 MHz, f _{CLK} = 16 MHz	V _{DD} = 5.0 V		0.95	3.7	mA
					V _{DD} = 3.0 V		0.95	3.7	mA
			Subsystem	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.47	0.89	μΑ
				fsub = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.33	0.70	μΑ
					Resonator connection		0.52	0.89	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	1.90	μΑ
					Resonator connection		0.60	2.09	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μΑ
					Resonator connection		0.73	2.99	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μΑ
				T _A = +85°C	Resonator connection		1.46	6.29	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μΑ
				T _A = +105°C	Resonator connection		3.23	15.7	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		7.20	45.2	μΑ
				T _A = +125°C	Resonator connection		7.53	45.5	μΑ
	I _{DD3} Note 6	STOP	T _A = -40°C				0.18	0.50	μΑ
		mode Note 8	T _A = +25°C				0.23	0.50	μΑ
		Note 8	T _A = +50°C	T _A = +50°C			0.27	1.70	μΑ
			T _A = +70°C				0.44	2.60	μΑ
			T _A = +85°C	T _A = +85°C			1.17	5.90	μΑ
			T _A = +105°C				2.94	15.3	μΑ
			T _A = +125°C				7.14	45.1	μA

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$ to 20 MHz
 - 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1						0.20		μА
RTC operating current	IRTC Notes 1, 2, 3						0.02		μА
12-bit interval timer operating current	 IT Notes 1, 2, 4						0.02		μА
Watchdog timer operating current	 WDT Notes 1, 2, 5	fı∟ = 15 kHz					0.22		μА
A/D converter operating current	IADC Notes 1, 6	When conversion maximum spee		Normal mode,	AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
A/D converter reference voltage current	ADREF Note 1						75.0		μА
Temperature sensor operating current	I _{TMPS} Note 1						75.0		μΑ
LVD operating current	LVDNotes 1, 7						0.08		μА
Self-programming operating current	IFSP Notes 1, 8						2.5	12.2	mA
Programmable	I _{PGA} Note 9				AV _{REFP} = V _{DD} = 5.0 V		0.21	0.37	mA
gain amplifier operating current					AV _{REFP} = V _{DD} = 3.0 V		0.18	0.35	mA
Comparator	I _{CMP} Note 10	When one com	parato	r channel is	AV _{REFP} = V _{DD} = 5.0 V		41.4	74	μА
operating current		operating			AV _{REFP} = V _{DD} = 3.0 V		37.2	71	μА
	IVREF	When one inter	nal ref	erence voltage	AV _{REFP} = V _{DD} = 5.0 V		14.8	31	μА
		circuit is operat	ing		AV _{REFP} = V _{DD} = 3.0 V		8.9	24	μА
Programmable	IREF Note 11				AV _{REFP} = V _{DD} = 5.0 V		3.2	6.1	μА
gain amplifier/ comparator reference current source					AVREFP = VDD = 3.0 V		2.9	4.9	μΑ
BGO operating current	I _{BGO} Note 12						2.50	12.2	mA
SNOOZE	I _{SNOZ} Note 1	A/D converter	The	mode is perform	ed ^{Note 13}		0.50	1.10	mA
operating current		operation		A/D conversion on the conversion of the conversi	operations are performed, $P = V_{DD} = 5.0 \text{ V}$		1.20	2.17	mA
		CSI/UART oper	ration				0.70	1.27	mA

(Notes and Remarks are listed on the next page.)

- Notes 1. Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fill operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IWDT, when the watchdog timer is operating.
 - **6.** Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, when the A/D converter is operating in operating mode or in HALT mode.
 - **7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of ldd, ldd or ldd and llvd when the LVD circuit is in operation.
 - **8.** Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - 12. Current flowing only during data flash rewrite.
 - 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is TA = 25°C
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

```
ICMP × 3 + IVREF + IPGA + IREF
= 41.4 [\mu A] × 3 + 14.8 [\mu A] × 1 + 210 [\mu A] + 3.2 [\mu A]
= 352.2 [\mu A]
```

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

```
ICMP × 2 + IIREF
= 41.4 [\mu A] × 2 + 3.2 [\mu A]
= 86.0 [\mu A]
```



3.4 AC Characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

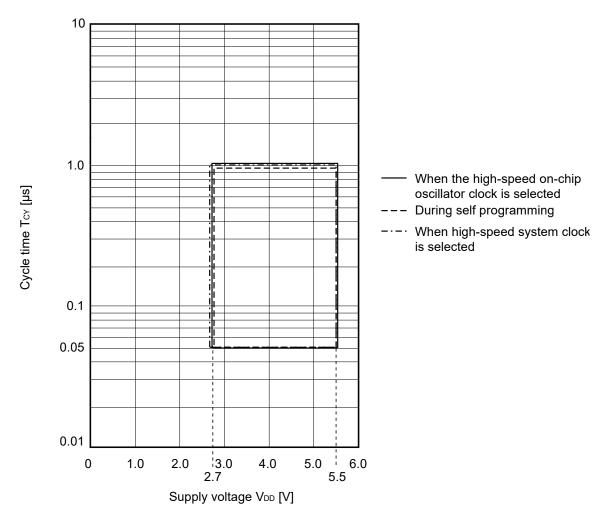
Items	Symbol	Cond	ditions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсч	Main system clock (f _{MAIN}) operation HS (high-speed main) mode		0.05		1	μs
		Subsystem clock (fsub)	operation	28.5	30.5	31.3	μS
		In the self programming main) mo mode		0.05		1	μs
External system clock frequency	fex			1.0		20.0	MHz
	fexs			32		35	kHz
External system clock input high-	texh, texl		24			ns	
level width, low-level width	texns, texts		13.7			μS	
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтıн, tтı∟			2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	f то	HS (high-speed main)	$4.0~V \leq V_{DD} \leq 5.5~V$			5	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)		mode	2.7 V ≤ V _{DD} < 4.0 V			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23	$2.7~V \leq V_{DD} \leq 5.5~V$	1			μs
RESET low-level width	trsL			10			μS

Remark fmck: Timer array unit operation clock frequency

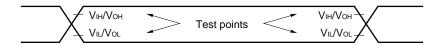
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

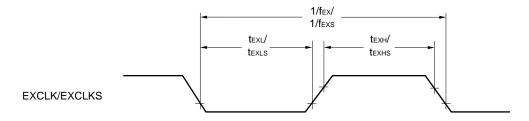
Tcy vs VDD (HS (high-speed main) mode)



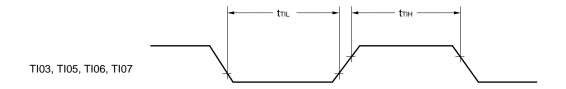
AC Timing Test Points

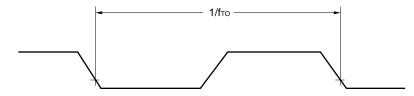


External System Clock Timing



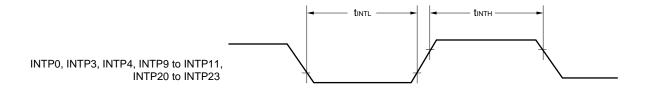
TI/TO Timing



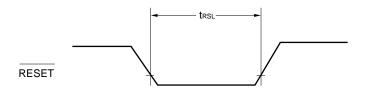


T003, T005, T006, TKB000, TKB001, TKB010, TKB011, TKB020, TKB021, TKC000 to TKC005

Interrupt Request Input Timing

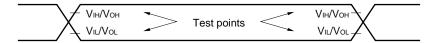


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode)

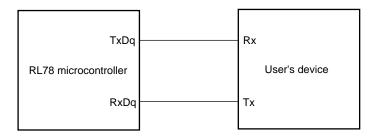
 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate ^{Note 1}					fмск/6	bps
			Theoretical value of the maximum transfer rate $$f_{\rm MCK}=f_{\rm CLK}{}^{\rm Note~2}$$		3.3	Mbps

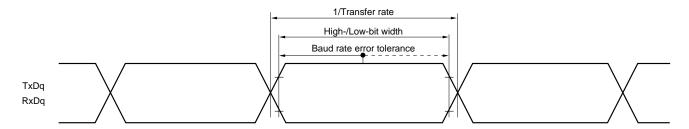
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 20 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		` ` `	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fclк	$4.0~V \leq V_{DD} \leq 5.5~V$	250		ns
			$2.7~V \leq V_{DD} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ V _{DD} ≤ 5.5 V t _{KC}		tkcy1/2 - 20		ns
	t _{KL1}	$2.7 \text{ V} \leq V_{DD} \leq 5.5$	5 V	tkcy1/2 - 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	4.0 V ≤ V _{DD} ≤ 5.5	5 V	80		ns
		$2.7 \text{ V} \leq V_{DD} \leq 5.5$	5 V	80		ns
SIp hold time (from SCKp↑)Note 2	t _{KSI1}			40		ns
Delay time from SCKp↓ to SOp outputNote 3	tkso1	C = 30 pF ^{Note 4}			80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

fMCK: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		, ,	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V$	fмcк ≤ 20 MHz	6/ f мск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	8/ f мск		ns
			fмcк ≤ 16 MHz	6/ƒмск		ns
SCKp high-/low-level width	tkH2,			tксу2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik2			1/fмск+40		ns
SIp hold time (from SCKp↑)Note 2	tksı2			1/fмск+60		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tĸso2	C = 30 pF ^{Note 4}			2/fмск+80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

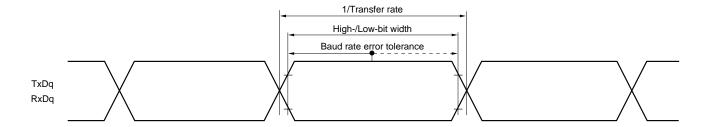
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

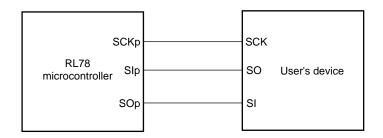
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

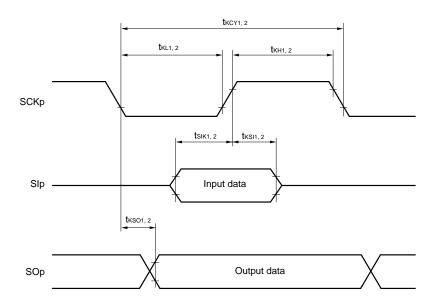
n: Channel number (mn = 00))



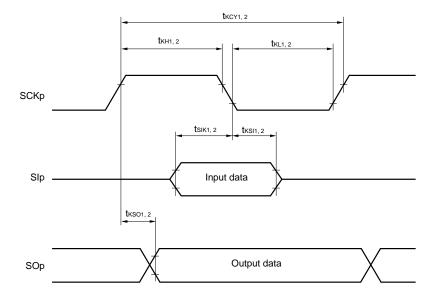
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions				Unit
					MIN.	MAX.	
Transfer rate		Reception	$ 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, $ $ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V} $			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps
						fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 20 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode	
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq V_{DD} \leq 5.5~V,$			Note 1	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 ^{Note 2}	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V},$			Note 3	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0~V \le V_{DD} \le 5.5~V$ and $2.7~V \le V_{b} \le 4.0~V$

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{[bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\left\{-C_b \times R_b \times \ln{(1-\frac{2.0}{V_b})}\right\} \times 3} \end{aligned} \text{ [bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

 $\mbox{\bf Remarks 1.} \quad \mbox{\bf Rb}[\Omega] \mbox{: Communication line (TxDq) pull-up resistance,} \\$

C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

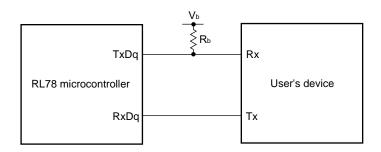
- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

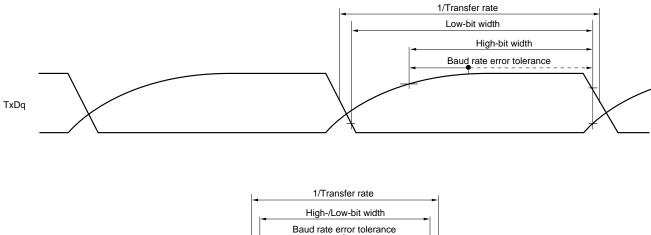
m: Unit number, n: Channel number (mn = 00 to 03))

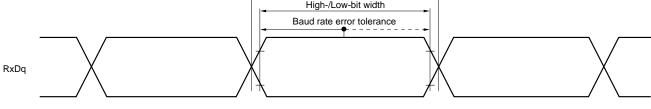


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +125^{\circ}\text{C}, \ 2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \ \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-sp Mo	-	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
			$ 2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega $	1000		ns
SCKp high-level width	t _{KH1}	$4.0 \text{ V} \leq \text{V}_{DD} \leq$ $C_b = 30 \text{ pF, F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$	tксү1/2 – 80		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$\begin{array}{l} 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ R_b = 2.7 \; k\Omega \end{array} \label{eq:basic_potential}$	tксу1/2 — 170		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$	tксу1/2 – 28		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$\begin{array}{l} 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ R_b = 2.7 \; k\Omega \end{array} \label{eq:basic_potential}$	tксү1/2 – 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le$ $C_b = 30 \text{ pF}, \text{ F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$	160		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$\begin{array}{l} 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ R_b = 2.7 \text{ k}\Omega \end{array}$	250		ns
SIp hold time tksi1 (from SCKp↑)Note 1		$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_\textrm{b} \leq 4.0~\textrm{V},$ $R_\textrm{b} = 1.4~\textrm{k}\Omega$	40		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$\begin{array}{l} 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ R_{\text{b}} = 2.7 \text{ k}\Omega \end{array}$	40		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le$ $C_b = 30 \text{ pF}, \text{ F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$		160	ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$\begin{array}{l} 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ R_b = 2.7 \; k\Omega \end{array} \label{eq:control_potential}$		250	ns
Slp setup time (to SCKp↓) ^{Note 2}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le$ $C_b = 30 \text{ pF}, \text{ F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_\textrm{b} \leq 4.0~\textrm{V},$ $R_\textrm{b} = 1.4~\textrm{k}\Omega$	80		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$\begin{array}{l} 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ R_b = 2.7 \; k\Omega \end{array} \label{eq:control_potential}$	80		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksi1	$4.0 \text{ V} \le \text{V}_{DD} \le$ $C_b = 30 \text{ pF}, \text{ F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$	40		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$\begin{array}{l} 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ R_b = 2.7 \text{ k}\Omega \end{array}$	40		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le$ $C_b = 30 \text{ pF}, \text{ F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $\textrm{R}_{\textrm{b}} = 1.4~\textrm{k}\Omega$		80	ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		80	ns n

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

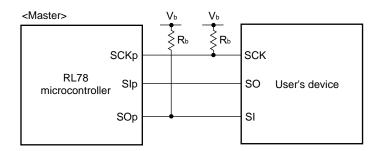
(Caution and Remarks are listed on the next page.)



Caution

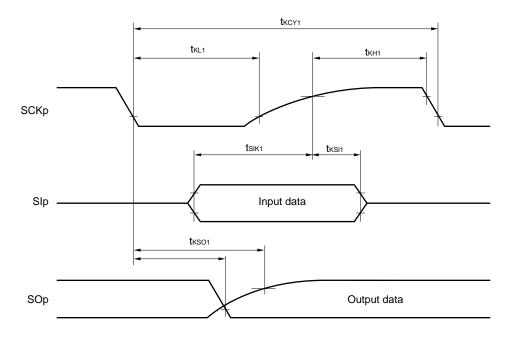
Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

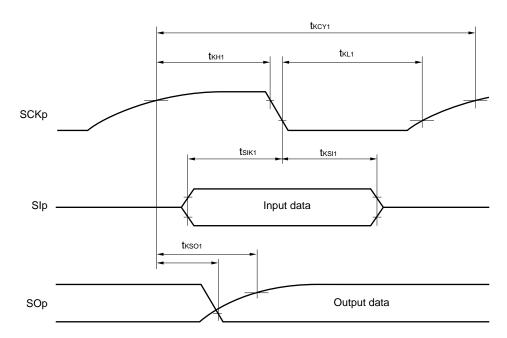


- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(6) DALI/UART4 mode

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate				fмск/12	bps
		Maximum transfer rate theoretical value fclk = 20 MHz, fmck = fclk		1.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register 4 (SPS4).)

3.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLκ≥ 1 MHz	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		μS
Hold time ^{Note 1}	thd:STA		4.0		μs
Hold time when SCLA0 = "L"	tLOW		4.7		μs
Hold time when SCLA0 = "H"	tніgн		4.0		μS
Data setup time (reception)	tsu:dat		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	μs
Setup time of stop condition	tsu:sto		4.0		μS
Bus-free time	t BUF		4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

(2) I²C fast mode

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

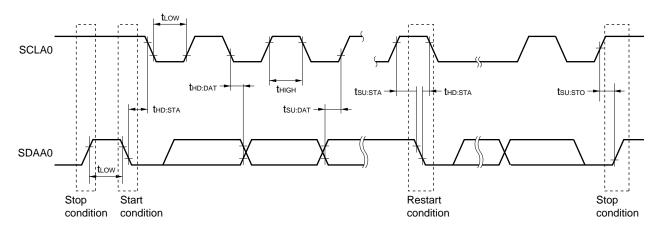
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fcLκ≥ 3.5 MHz	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		μS
Hold time ^{Note 1}	thd:sta		0.6		μS
Hold time when SCLA0 = "L"	tLow		1.3		μS
Hold time when SCLA0 = "H"	tніgн		0.6		μS
Data setup time (reception)	tsu:dat		100		ns
Data hold time (transmission)Note 2	thd:dat		0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		μS
Bus-free time	tBUF		1.3		μS

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 3.6.1 (1).	See 3.6.1 (3).	See 3.6.1 (4) .
ANI16 to ANI19	See 3.6.1 (2) .		
Internal reference voltage Temperature sensor output voltage	See 3.6.1 (1).		-

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	s	MIN.	TYP.	MAX.	Unit		
Resolution	RES			8		10	bit		
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±3.5	LSB		
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS		
		Target pin: ANI2, ANI4 to ANI7	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.4		39	μs		
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS		
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ VDD ≤ 5.5 V	3.8		39	μs		
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR		
Full-scale errorNotes 1, 2	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR		
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB		
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB		
Analog input voltage	Vain	ANI2, ANI4 to ANI7		0		AVREFP	V		
		Internal reference voltage (HS (high-speed main) mode	V _{BGR} Note 4			٧			
		Temperature sensor output vo (HS (high-speed main) mode	emperature sensor output voltage			V _{TMPS25} Note 4			

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to ANI19	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	3.4		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.2\%$ FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}, \text{ Reference voltage (+)} = V_{DD}, \text{ Reference voltage (-)} = V_{SS})$

-							
Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.4		39	μs
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.8		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale errorNotes 1, 2	E _F S	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI2, ANI4 to ANI7	,	0		V _{DD}	V
		ANI16 to ANI19		0		V _{DD}	V
		Internal reference voltage (HS (high-speed main) mod		V			
		Temperature sensor output (HS (high-speed main) mod	mperature sensor output voltage				V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

^{2.} This value is indicated as a ratio (%FSR) to the full-scale value.

^{3.} See 3.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGR^{Note 3}, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity errorNote 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		V _{BGR} Note 3	٧

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.
- **4.** When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvтмрs	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

3.6.3 Programmable gain amplifier

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	S				±1.5	%
		32 time	s				±2	%
Slew rate ^{Note 1}	SRRPGA	Rising edge	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	4			V/μs
				16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SRFPGA	Falling	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait timeNote 2	t PGA	4, 8 tim	4, 8 times					μs
		16, 32 t	imes		10			μS

Notes 1. When V_{IPGA} = 0.1V_{DD}/gain to 0.9V_{DD}/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

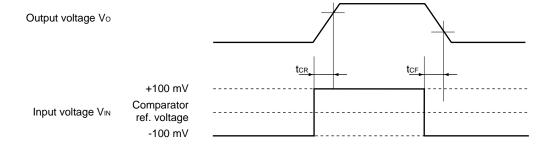
3.6.4 Comparator

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{REFP} = \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	٧
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait timeNote 1	tcmp	$3.3~V \leq V_{DD} \leq 5.5~V$	1			μs
		2.7 V ≤ V _{DD} < 3.3 V	3			μs
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μs

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.

Remark These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.

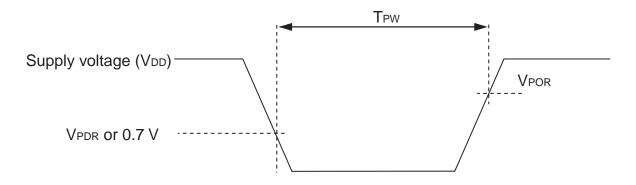


3.6.5 POR circuit characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.62	٧
	V _{PDR}	Power supply fall time	1.44	1.50	1.61	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.97	4.06	4.25	V
voltage			Power supply fall time	3.89	3.98	4.15	V
		V _{LVD1}	Power supply rise time	3.67	3.75	3.93	V
			Power supply fall time	3.59	3.67	3.83	V
		V _{LVD2}	Power supply rise time	3.06	3.13	3.28	V
			Power supply fall time	2.99	3.06	3.20	V
		V _{LVD3}	Power supply rise time	2.95	3.02	3.17	V
			Power supply fall time	2.89	2.96	3.09	V
		V _{LVD4}	Power supply rise time	2.85	2.92	3.07	V
			Power supply fall time	2.79	2.86	2.99	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.95	V
			Power supply fall time	2.70	2.75	2.88	V
Minimum pu	ulse width	tw		300			μS
Detection de	elay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVD0}	VPOC2, V	POC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage: 2.7 V			2.75	2.88	V
mode	V _{LVD1}	L	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	3.07	V
				Falling interrupt voltage	2.79	2.86	2.99	V
	V _{LVD2}	L	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
				Falling interrupt voltage	2.89	2.96	3.09	V
	V _{LVD3}	L	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.25	V
				Falling interrupt voltage	3.89	3.98	4.15	V

3.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SV _{DD}				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 33.4 AC Characteristics.

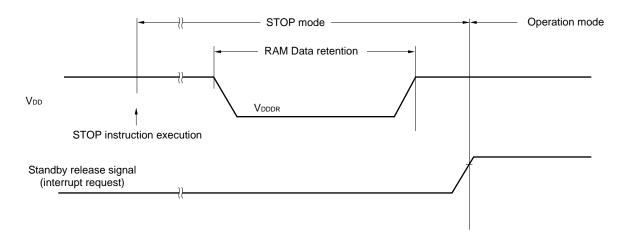
3.7 RAM Data Retention Characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltageNote 2	VDDDR		1.47 ^{Note 1}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.



3.8 Flash Memory Programming Characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7~V \le V_{DD} \le 5.5~V$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3, 4}	1,000			Times
Number of data flash		Retained for 1 year, T _A = 25°C ^{Note 3, 4}		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, T _A = 85°C ^{Note 3, 4}	100,000			
		Retained for 20 years, T _A = 85°C ^{Note 3, 4}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- **4.** These are the average temperature of during the retainment.

3.9 Dedicated Flash Memory Programmer Communication (UART)

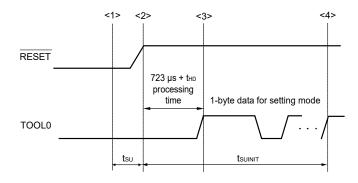
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



<R>

- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

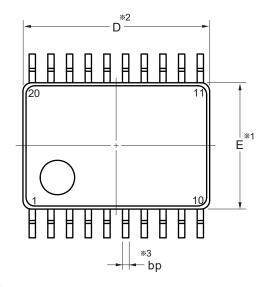
4. PACKAGE DRAWINGS

<R>

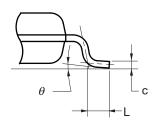
4.1 20-pin Products

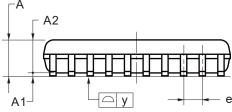
R5F1076CGSP#V0, R5F1076CGSP#X0, R5F1076CMSP#V0, R5F1076CMSP#X0

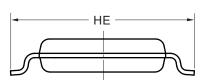
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end







NOTE

- 1.Dimensions "X1" and "X2" do not include mold flash.
- 2.Dimension " $\mbox{\ensuremath{\%}}3$ " does not include trim offset.

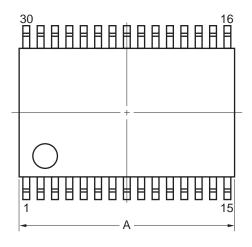
	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
Е	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	$0.22 + 0.10 \\ -0.05$
С	$0.15 \pm 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

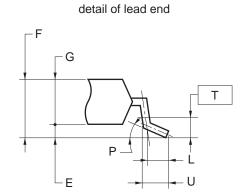
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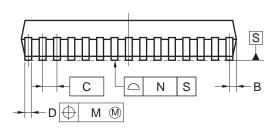
4.2 30-pin Products

R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0, R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

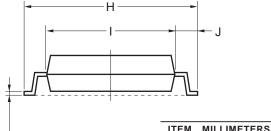






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



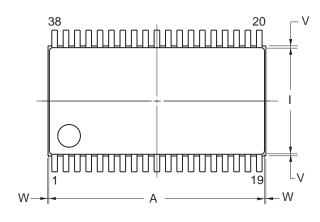
HEIVI	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
- 1	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15

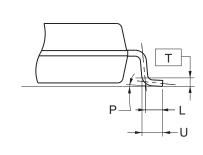
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4.3 38-pin Products

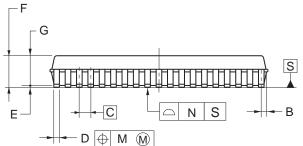
R5F107DEGSP#V0, R5F107DEGSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0

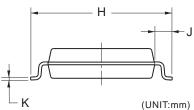
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-SSOP38-0300-0.65	PRSP0038JA-A	P38MC-65-2A4-2	0.3





detail of lead end





NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

	(UNIT.IIIII)
ITEM	DIMENSIONS
Α	12.30±0.10
В	0.30
С	0.65 (T.P.)
D	$0.32^{+0.08}_{-0.07}$
Е	0.125±0.075
F	2.00 MAX.
G	1.70±0.10
Н	8.10±0.20
I	6.10±0.10
J	1.00±0.20
K	$0.17^{+0.08}_{-0.07}$
L	0.50
М	0.10
N	0.10
Р	3°+7°
Т	0.25(T.P.)
U	0.60±0.15
V	0.25 MAX.
W	0.15 MAX.

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Revision History	RL78/I1A Datasheet
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			Description		
Rev.	Date	Page	Summary		
3.20	Sep 29, 2017	p.1	Modification of description in 1.1 Features		
		p.59	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes		
		p.102	Modification of figure in 3.10 Timing of Entry to Flash Memory Programming Modes		
		p.103	Modification of figure in 4.1 20-pin Products		

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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